

FIG.1

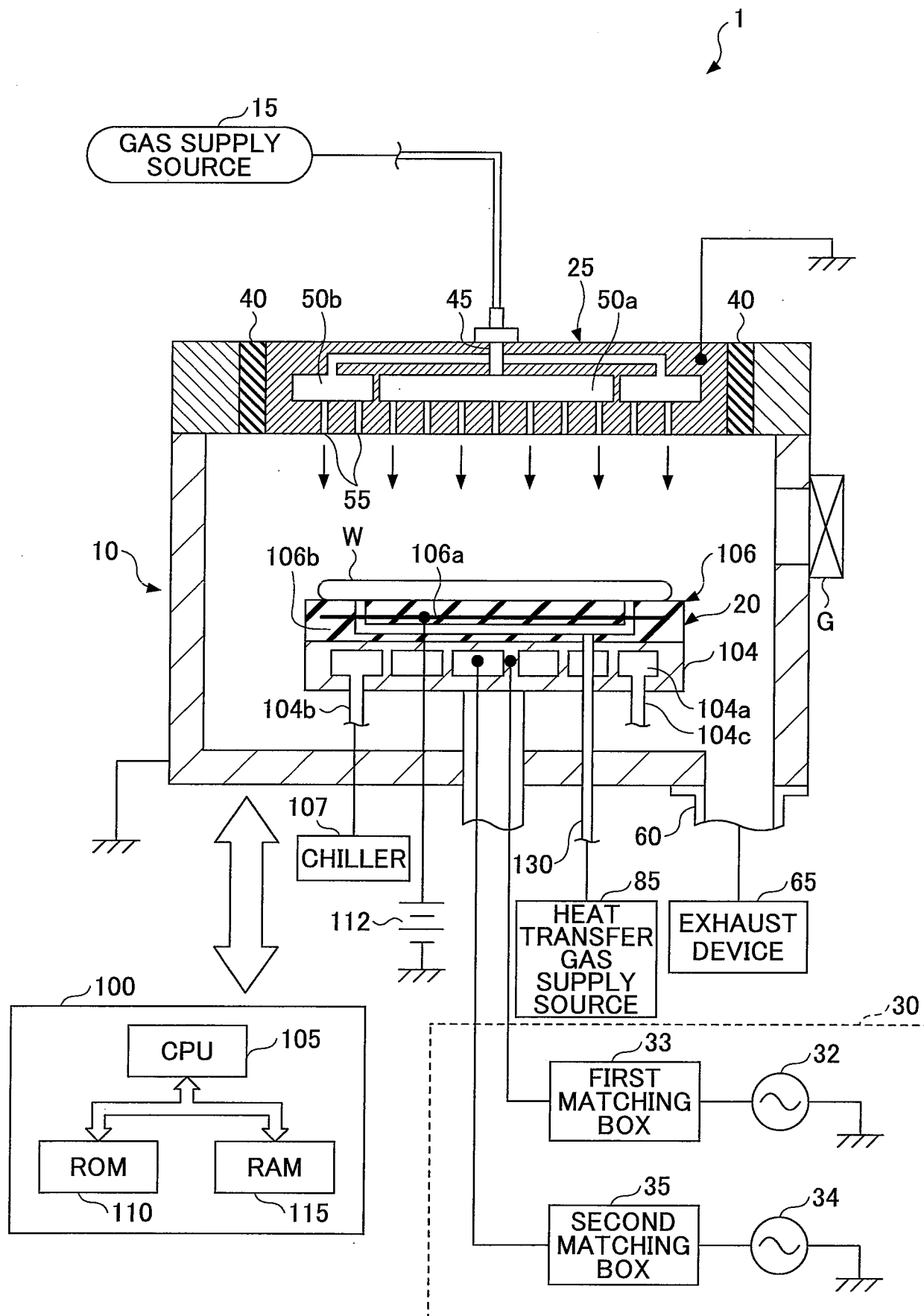


FIG.2

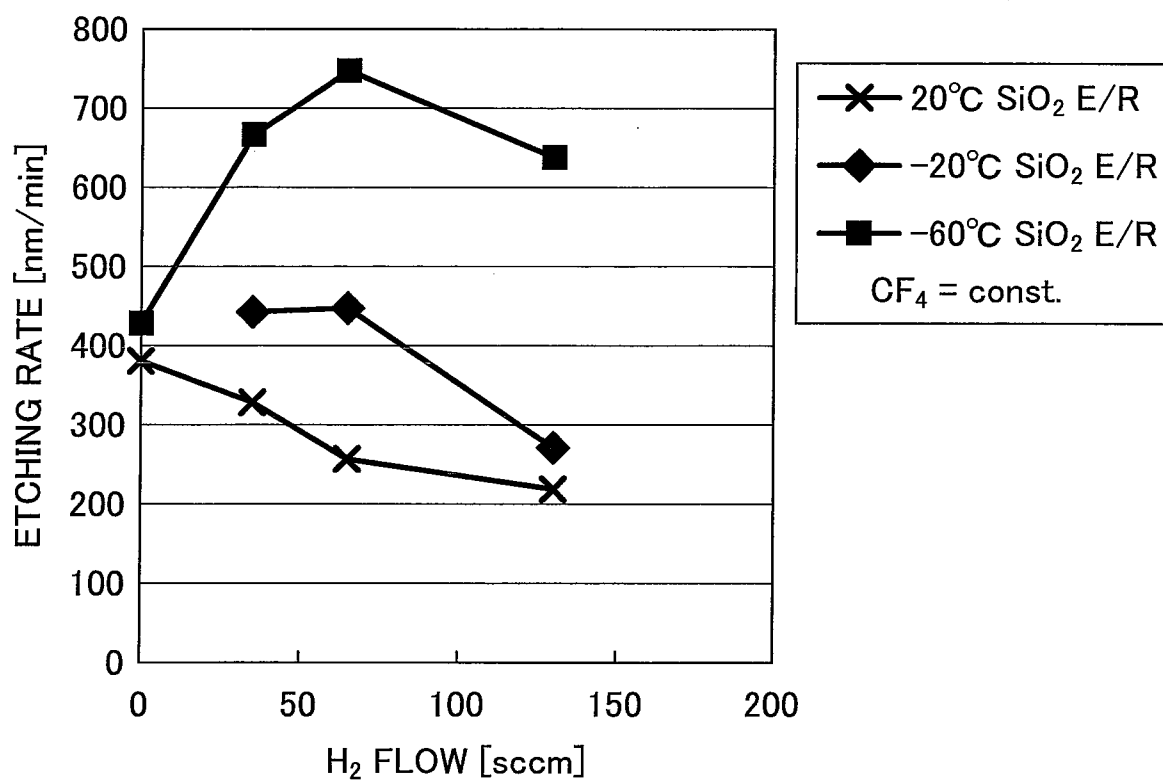


FIG.3

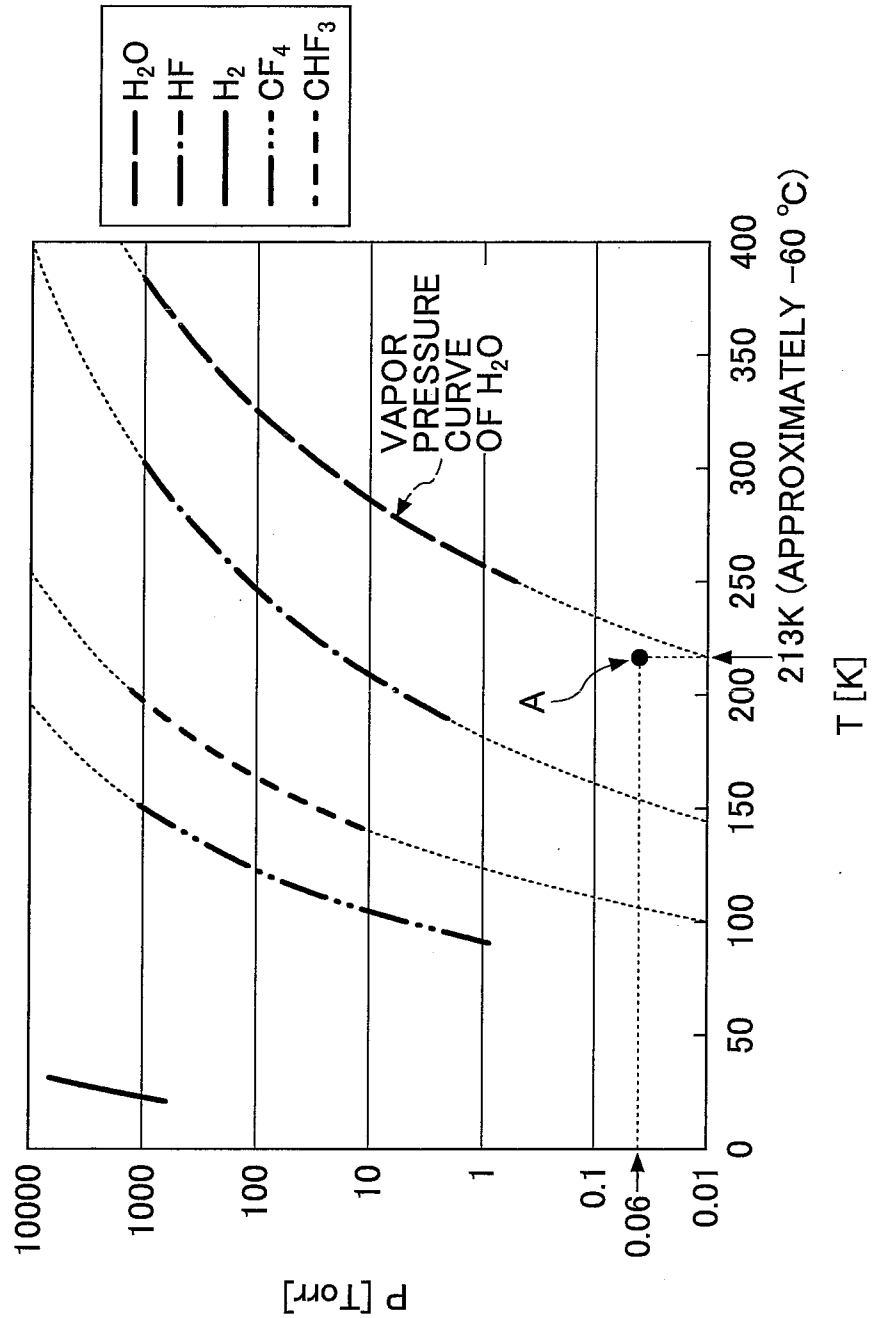


FIG.4

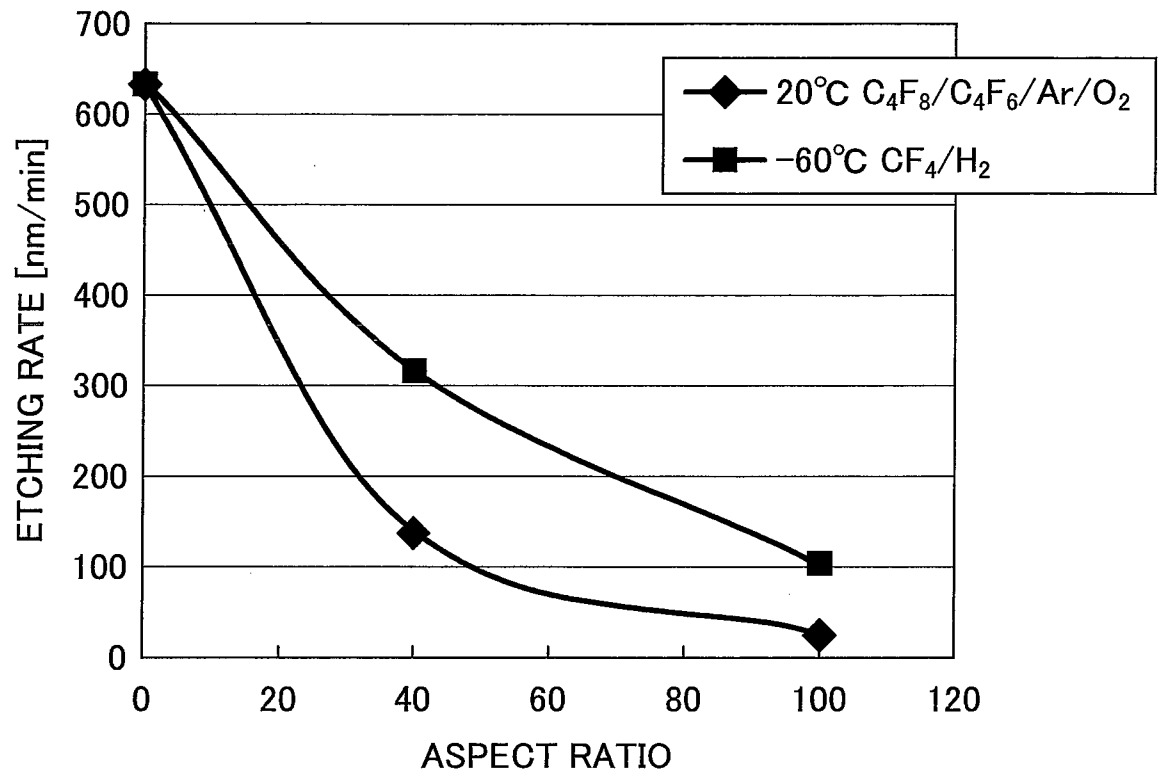


FIG.5

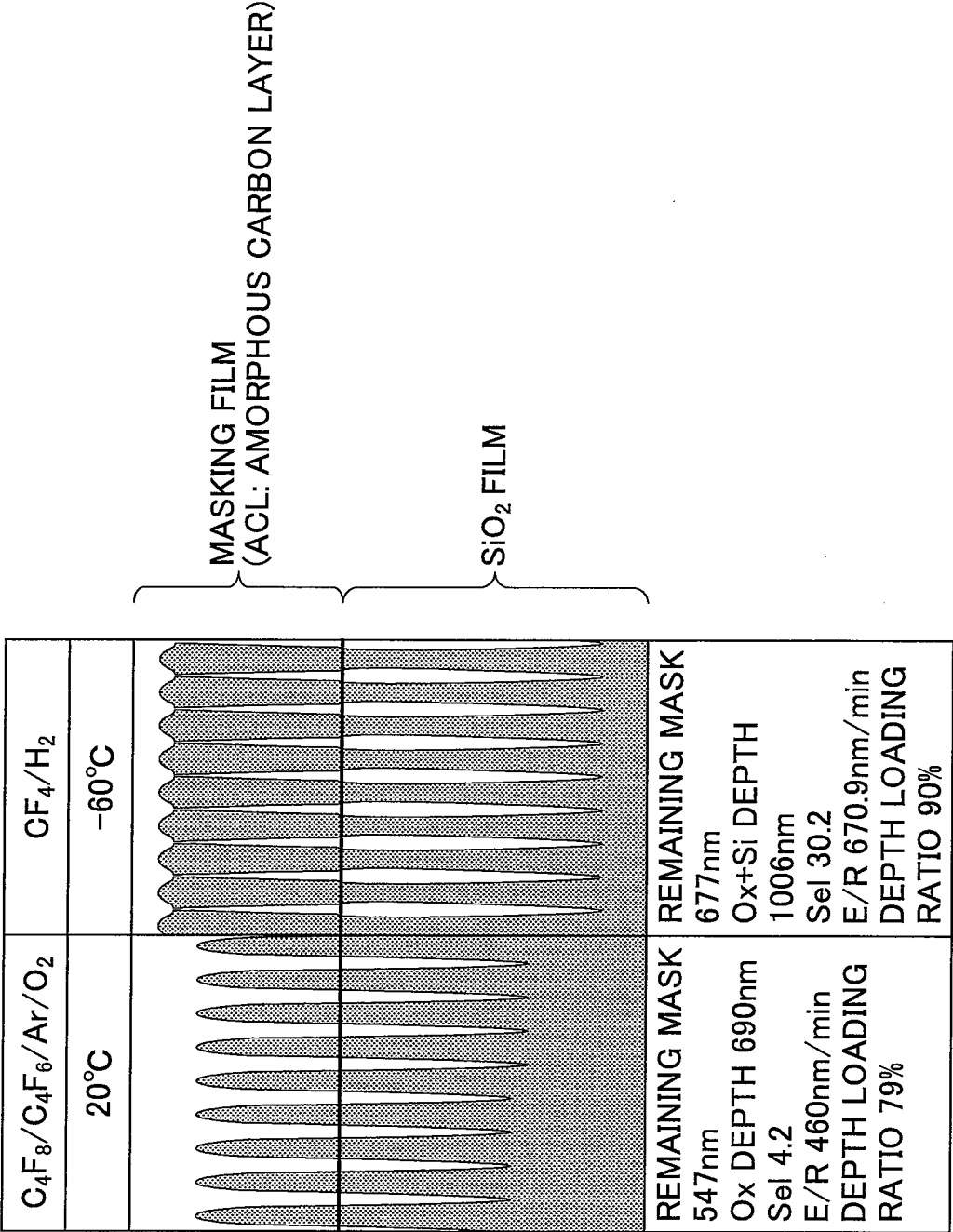


FIG.6A

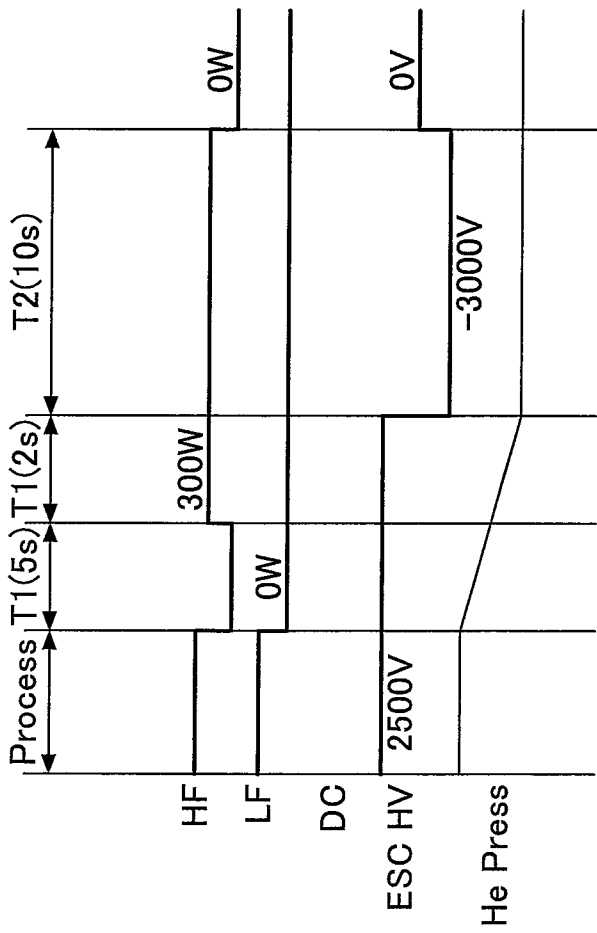


FIG.6B

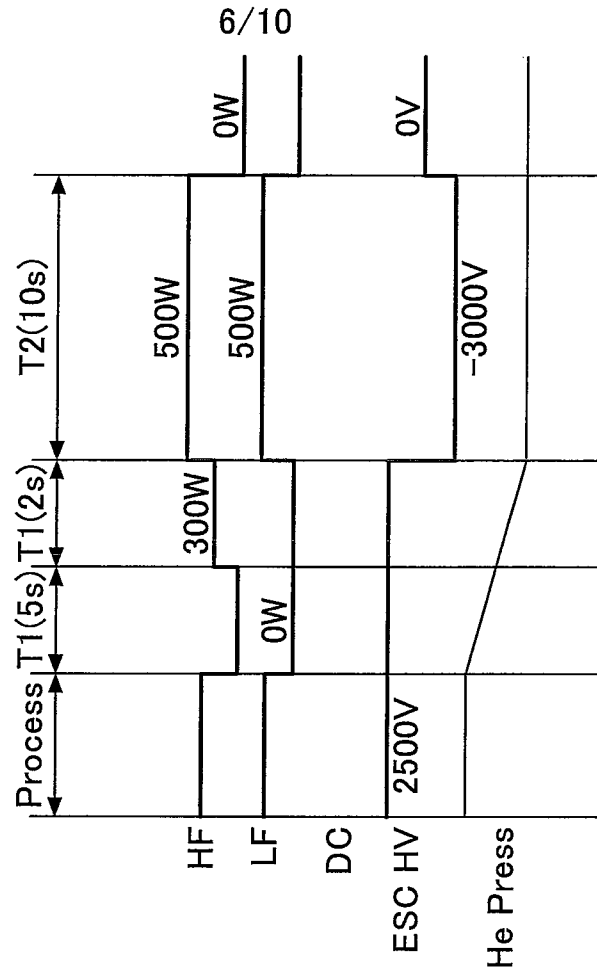


FIG.7

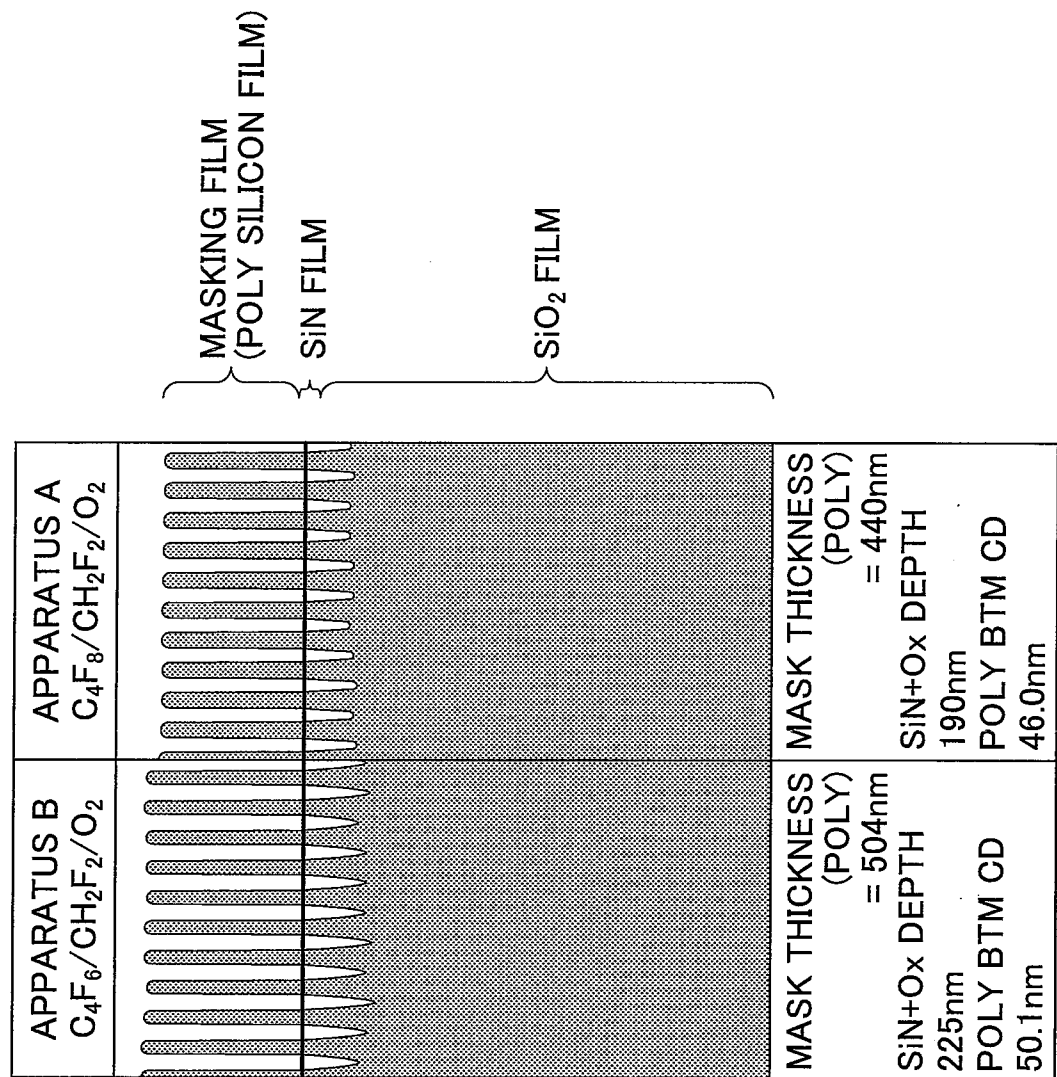
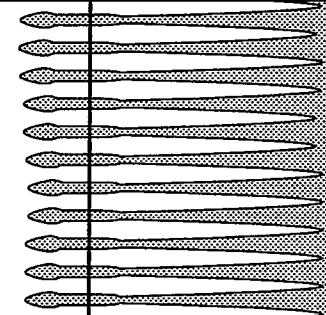
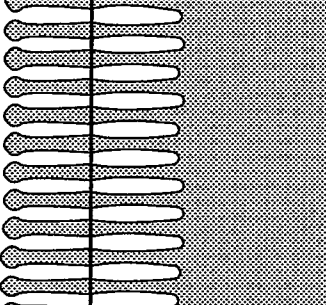
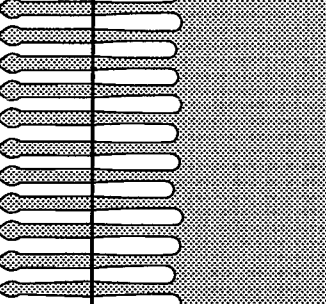
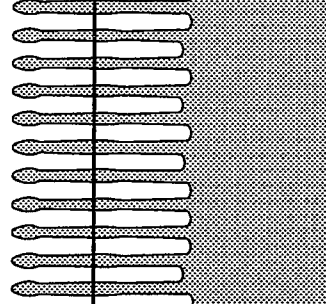


FIG.8

APPARATUS B CF ₄ /H ₂		APPARATUS A CF ₄ /H ₂	
 ELECTROSTATIC CHUCK (ALUMINUM) + CHILLER (-60°C)	 ELECTROSTATIC CHUCK (TITANIUM) + CHILLER (-60°C)	 ELECTROSTATIC CHUCK (TITANIUM) + CHILLER (-60°C) + HEAT TRANSFER GAS (40Torr)	
REMAINING MASK 224nm SiN+Ox DEPTH 842nm Sel 2.2 E/R 617nm/min	REMAINING MASK 295nm SiN+Ox DEPTH 333nm Sel 0.5 E/R 108.0nm/min	REMAINING MASK 331nm SiN+Ox DEPTH 321nm Sel 2.1 E/R 154nm/min	REMAINING MASK 270nm SiN+Ox DEPTH 379nm Sel 1.7 E/R 192.7nm/min

} MASKING FILM
(POLY SILICON FILM)
} SiN FILM
} SiO₂ FILM

FIG.9

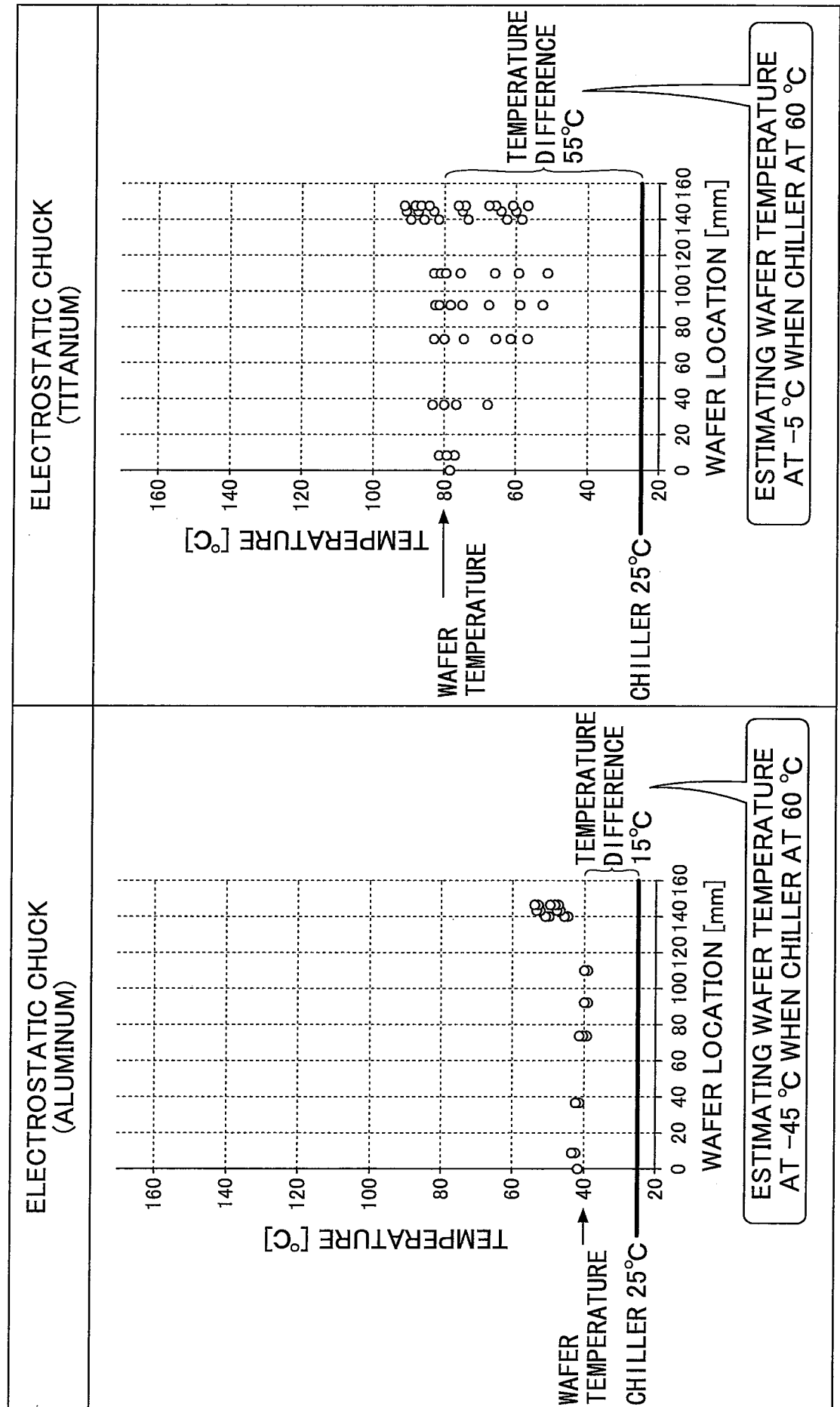


FIG.10

